

TO-220 Plastic-Encapsulate Transistors

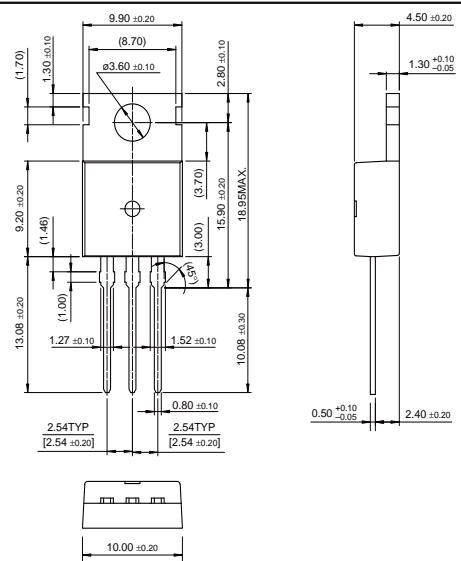
FEATURES

- NPN Silicon Transistor
- High speed Switching
- Suitable for Switching Regulator and Motor Control
- High Voltage Mode Application

MECHANICAL DATA

- Case style:TO-220 molded plastic
- Mounting position:any

TO-220



Unit: inch (mm)

MAXIMUM RATINGS

(Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	BVCBO	700	V
Collector-Emitter Voltage	BVCEO	400	V
Emitter-Base Voltage	BVEBO	9	V
Collector Current	Ic	12	A
Collector Power Dissipation	Pc	100	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55~150	°C

Electrical Characteristics (Ta=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Collector-base breakdown voltage	BVCBO	Ic = 100µA, Ie = 0	700			V
Collector-emitter breakdown voltage	BVCEO	Ic = 10mA, Ib = 0	400			V
Emitter-base breakdown voltage	BVEBO	Ie = 100µA, Ic = 0	9			V
Collector cut-off current	Icbo	Vcb = 700V, Ie = 0			0.1	mA
Collector cut-off current	Iceo	Vce = 400V, Ib = 0			1	mA
Emitter cut-off current	Ieb	Ve = 9V, Ic = 0			0.1	mA
*DC current gain	hFE	Vce = 5V, Ic = 5A Vce = 5V, Ic = 8A	8 6		40 30	
*Collector-emitter saturation voltage	Vce (sat)	Ic = 5A, Ib = 1A Ic = 8A, Ib = 1.6A Ic = 12A, Ib = 3A			1 1.5 3	V
*Base -emitter saturation voltage	Vbe (sat)	Ic = 5A, Ib = 1A Ic = 8A, Ib = 1.6A			1.2 1.6	V
Transition frequency	fT	Vce = 10V, Ib = 0.5A	4			MHz
Turn On Time	tON	Vcc = 125V, Ic = 8A			1.1	µs
Storage Time	tSTG	Ib1 = 1.6A, Ib2 = -1.6A			3.0	µs
Fall Time	tF	Rl = 15.6Ω			0.7	µs

* Pulse Test: Pulse Width ≤ 300µS, Duty Cycle ≤ 2%